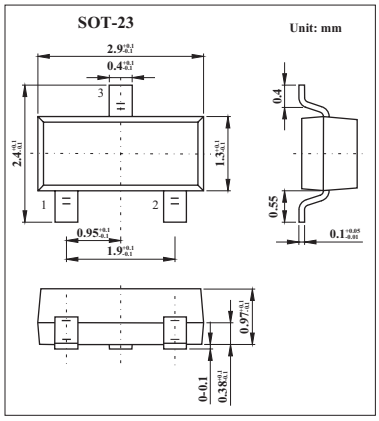
High Conductance Ultra Fast Diode

MMBD1201;MMBD1203
MMBD1204;MMBD1205



■ Features

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	50	V
Average Rectified Current	I_O	200	mA
DC Forward Current	I_F	600	mA
Recurrent Peak Forward Current	i_f	700	mA
Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	$i_{f(surge)}$	 1.0 2.0	 A A
Storage Temperature Range	T_{stg}	-55 to + 150	℃
Operating Junction Temperature	T_J	150	℃
Total Device Dissipation Derate above 25 ℃	P_D	350 2.8	mW mW / ℃
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	℃ /W

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown voltage	B_V	I_R = 100 μA	100		V
Reverse current	I_R	I_F = 20 V		25	nA
		I_F = 50 V		50	nA
		I_F = 50 V, T_A = 150 ℃		5	μA
Forward voltage	V_F	I_F = 1.0 mA	550	600	mV
		I_F = 10 mA	660	740	mV
		I_F = 100 mA	820	920	mV
		I_F = 200 mA	0.87	1.0	V
		I_F = 300 mA		1.1	V
Diode capacitance	C_D	V_R = 0, f = 1.0 MHz		2.0	pF
Reverse recovery time	T_{RR}	I_F = I_R = 10 mA,I_{RR} = 1.0 mA, R_L = 100 Ω		4.0	ns

■ Marking

Type	MMBD1201	MMBD1203	MMBD1204	MMBD1205
Marking	24	26	27	28